

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1-15. (Canceled).

16. (Currently amended) A substrate treatment method comprising:

coating a substrate with a photosensitive resist film;

exposing said photosensitive resist film;

supplying a reducing solution to the surface of said exposed photosensitive resist film and performing a pretreatment;

developing the photosensitive resist film subjected to said pretreatment; and

supplying a cleaning solution to said substrate, and cleaning the substrate.

17. (Original) The substrate treatment method according to claim 16, wherein the reducing solution is an aqueous solution containing at least one of hydrogen, H_2S , HNO_3 , and H_2SO_3 .

18. (Original) The substrate treatment method according to claim 16, further comprising: discharging the developing solution to said photosensitive resist film from a developing solution supply nozzle; relatively moving said substrate and said developing solution supply nozzle; forming a developing solution film on the surface of the photosensitive resist film; and developing said photosensitive resist film.

19. (Original) The substrate treatment method according to claim 18, further comprising: agitating said developing solution film; and developing said photosensitive resist film.

20. (Original) The substrate treatment method according to claim 16, further comprising: removing said reducing solution from the surface of said photosensitive resist film after said pretreatment; drying the surface of the resist film; and developing said photosensitive resist film.

21. (Original) The substrate treatment method according to claim 18, further comprising: forming said developing solution film on the resist film surface in a state in which said reducing solution remains on the surface of said photosensitive resist film after said pretreatment; agitating the remaining solution and the developing solution; and developing said photosensitive resist film.

22-37. (Canceled).

38. (Currently amended) A manufacturing method of a semiconductor device, comprising:

coating a substrate with a photosensitive resist film;

exposing said photosensitive resist film;

supplying a reducing solution to the surface of said exposed photosensitive resist film and performing a pretreatment;

developing the photosensitive resist film subjected to said pretreatment; and

supplying a cleaning solution onto said substrate, and cleaning the substrate.

39-43. (Canceled).